



FDS2672

N-Channel UltraFET Trench® MOSFET

200V, 3.9A, 70mΩ

Features

- Max $r_{DS(on)}$ = 70mΩ at $V_{GS} = 10V$, $I_D = 3.9A$
- Max $r_{DS(on)}$ = 80mΩ at $V_{GS} = 6V$, $I_D = 3.5A$
- Fast switching speed
- High performance trench technology for extremely low $r_{DS(on)}$
- RoHS compliant

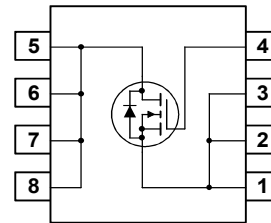
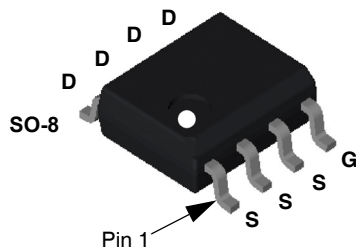


General Description

This single N-Channel MOSFET is produced using Fairchild Semiconductor's advanced UltraFET Trench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Application

- DC-DC conversion



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Rated | Units |
|----------------|--|------------|------------------|
| V_{DS} | Drain to Source Voltage | 200 | V |
| V_{GS} | Gate to Source Voltage | ± 20 | V |
| I_D | Drain Current -Continuous (Note 1a) | 3.9 | A |
| | -Pulsed | 50 | |
| E_{AS} | Single Pulse Avalanche Energy (Note 3) | 37.5 | mJ |
| P_D | Power Dissipation (Note 1a) | 2.5 | W |
| | Power Dissipation (Note 1b) | 1.0 | |
| T_J, T_{STG} | Operating and Storage Temperature | -55 to 150 | $^\circ\text{C}$ |

Thermal Characteristics

| | | | |
|-----------------|---|-----|---------------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case (Note 1) | 25 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1a) | 50 | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 1b) | 125 | |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape Width | Quantity |
|----------------|---------|-----------|------------|------------|
| FDS2672 | FDS2672 | 13" | 12mm | 2500 units |

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

Off Characteristics

| | | | | | | |
|--------------------------------------|---|--|-----|-----|-----------|--------------------------------|
| BV_{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 200 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, referenced to 25°C | | 206 | | $\text{mV}/^\circ\text{C}$ |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 160\text{V}, V_{GS} = 0\text{V}$ $V_{DS} = 160\text{V}, V_{GS} = 0\text{V}, T_J = 55^\circ\text{C}$ | | | 1 10 | μA μA |
| I_{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |

On Characteristics (Note 2)

| | | | | | | |
|--|--|---|---|-----|-----|----------------------------|
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250\mu\text{A}$ | 2 | 2.9 | 4 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D = 250\mu\text{A}$, referenced to 25°C | | -11 | | $\text{mV}/^\circ\text{C}$ |
| $r_{DS(on)}$ | Drain to Source On Resistance | $V_{GS} = 10\text{V}, I_D = 3.9\text{A}$ | | 59 | 70 | m Ω |
| | | $V_{GS} = 6\text{V}, I_D = 3.5\text{A}$ | | 63 | 80 | |
| | | $V_{GS} = 10\text{V}, I_D = 3.9\text{A}, T_J = 125^\circ\text{C}$ | | 124 | 148 | |
| g_{FS} | Forward Transconductance | $V_{DS} = 10\text{V}, I_D = 3.9\text{A}$ | | 15 | | S |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|--|-------------------|------|------|----------|
| C_{iss} | Input Capacitance | $V_{DS} = 100\text{V}, V_{GS} = 0\text{V},$ $f = 1\text{MHz}$ | | 1905 | 2535 | pF |
| C_{oss} | Output Capacitance | | | 100 | 135 | pF |
| C_{rss} | Reverse Transfer Capacitance | | | 30 | 45 | pF |
| R_g | Gate Resistance | | $f = 1\text{MHz}$ | 0.7 | | Ω |

Switching Characteristics

| | | | | | | |
|--------------|-------------------------------|---|--|----|----|----|
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD} = 100\text{V}, I_D = 3.9\text{A}$ $V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$ | | 22 | 35 | ns |
| t_r | Rise Time | | | 10 | 20 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 35 | 56 | ns |
| t_f | Fall Time | | | 10 | 20 | ns |
| $Q_g(TOT)$ | Total Gate Charge at 10V | | | 33 | 46 | nC |
| Q_{gs} | Gate to Source Gate Charge | $V_{DD} = 100\text{V}, I_D = 3.9\text{A}$ | | 11 | | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | | | 7 | | nC |

Drain-Source Diode Characteristics

| | | | | | | |
|----------|-------------------------------|--|--|------|-----|----|
| V_{SD} | Source to Drain Diode Voltage | $V_{GS} = 0\text{V}, I_S = 3.9\text{A}$ | | 0.75 | 1.2 | V |
| t_{rr} | Reverse Recovery Time | $I_F = 3.9\text{A}, di/dt = 100\text{A}/\mu\text{s}$ | | 67 | 101 | ns |
| Q_{rr} | Reverse Recovery Charge | $I_F = 3.9\text{A}, di/dt = 100\text{A}/\mu\text{s}$ | | 179 | 269 | nC |

Notes:

1: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



Scale 1:1 on letter size paper

a) $50^\circ\text{C}/\text{W}$ (10 sec)
 $62.5^\circ\text{C}/\text{W}$ steady state
when mounted on a 1in^2
pad of 2 oz copper



b) $125^\circ\text{C}/\text{W}$ when mounted on a
minimum pad.

2: Pulse Test: Pulse Width < 300 us, Duty Cycle < 2.0%.
3: Starting $T_J = 25^\circ\text{C}$, $L = 3\text{mH}$, $I_{AS} = 5\text{A}$, $V_{DD} = 100\text{V}$, $V_{GS} = 10\text{V}$

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

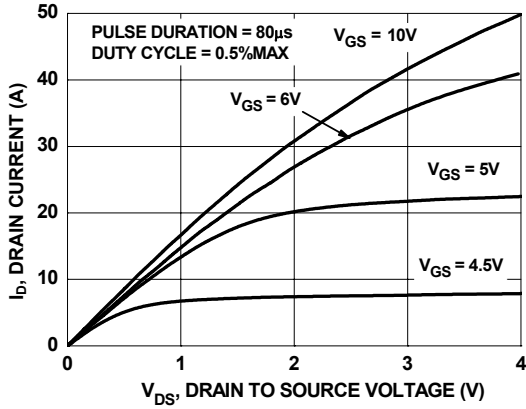


Figure 1. On Region Characteristics

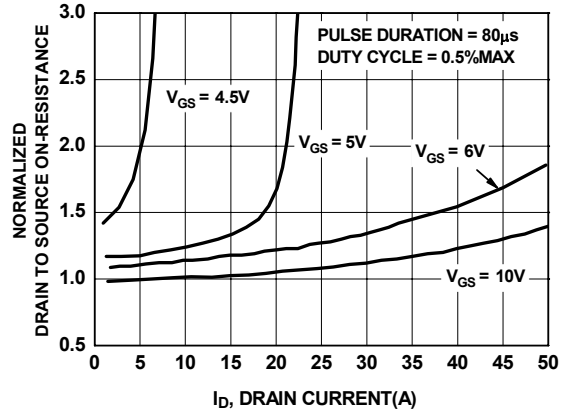


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

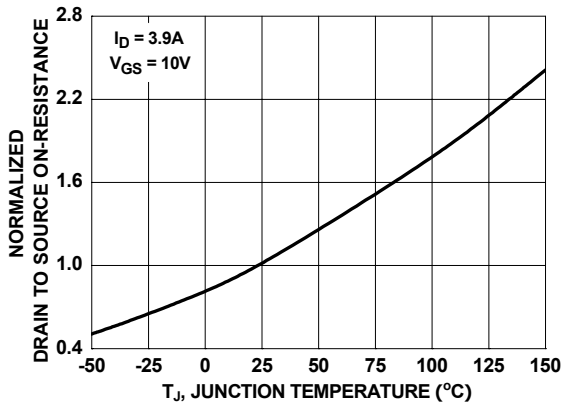


Figure 3. Normalized On Resistance vs Junction Temperature

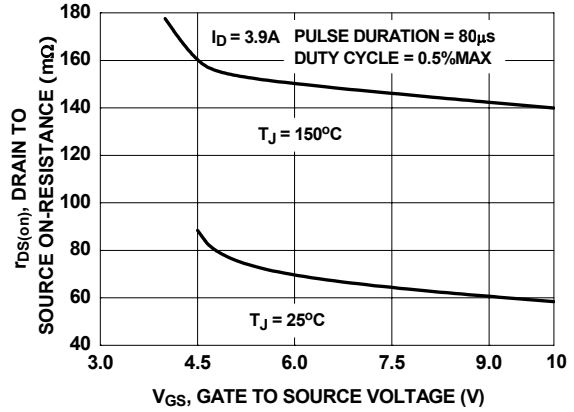


Figure 4. On-Resistance vs Gate to Source Voltage

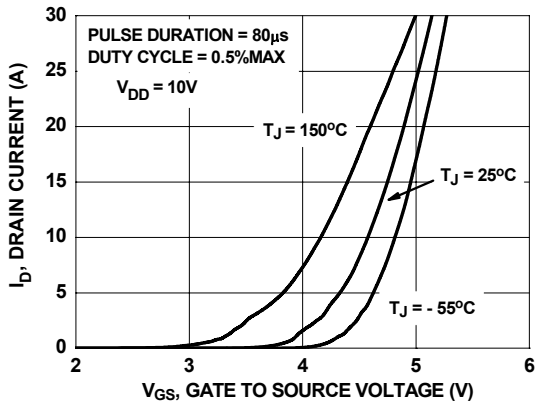


Figure 5. Transfer Characteristics

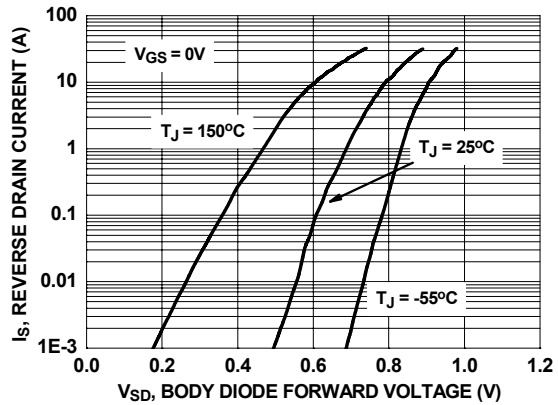


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

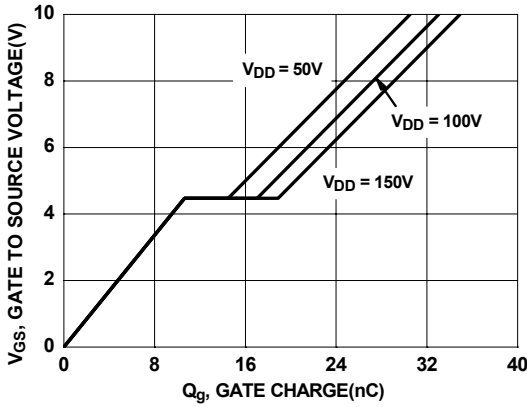


Figure 7. Gate Charge Characteristics

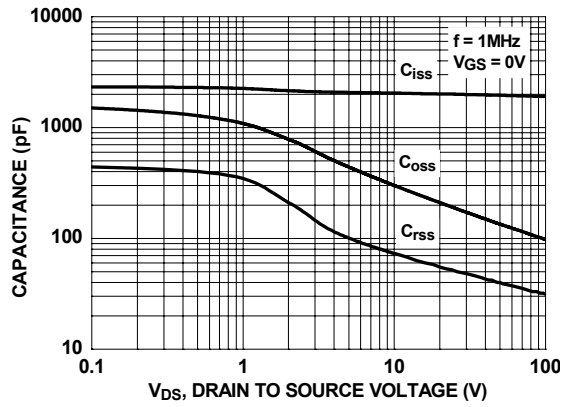


Figure 8. Capacitance vs Drain to Source Voltage

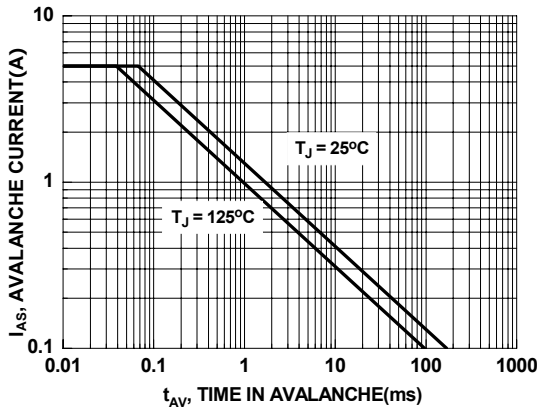


Figure 9. Unclamped Inductive Switching Capability

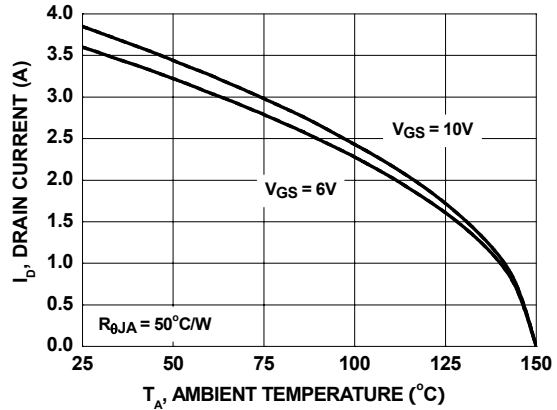


Figure 10. Ambient Continuous Drain Current vs Case Temperature

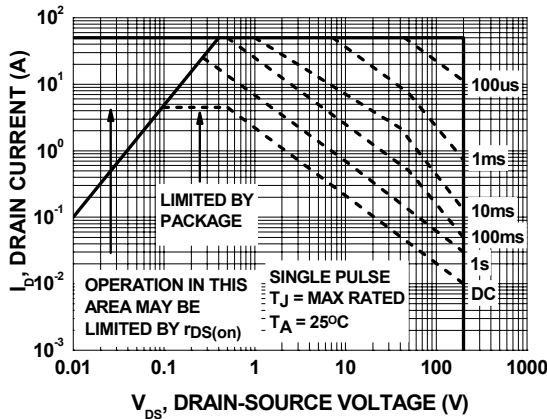


Figure 11. Forward Bias Safe Operating Area

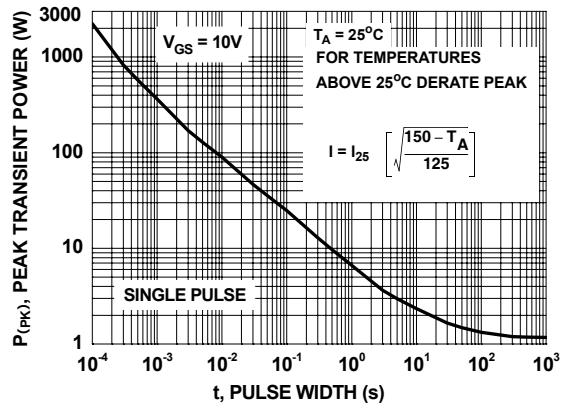


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

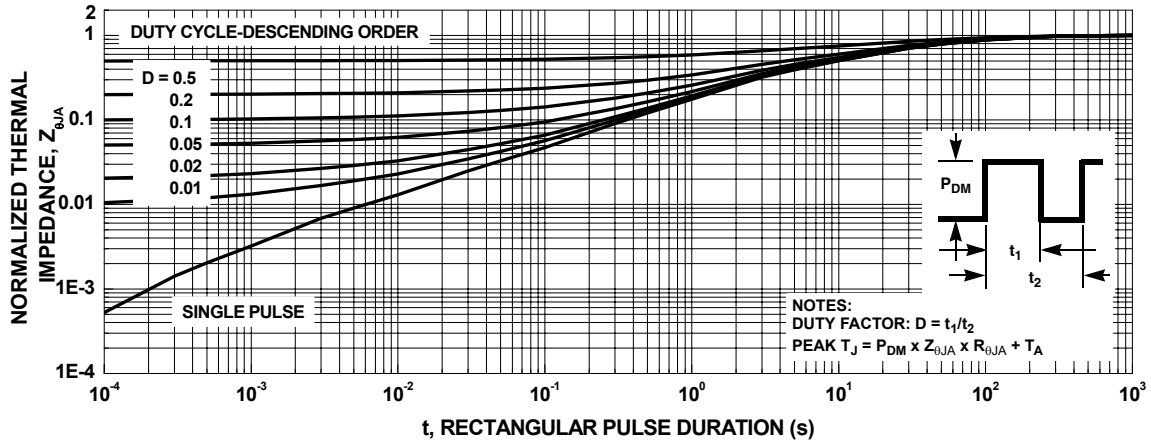


Figure 13. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b
 Transient thermal response will change depending on the circuit board design

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